



DMN2310UT

Product Summary

BV _{DSS}	Rds(on)	ID TA = +25°C
20V	240mΩ @ V _{GS} = 4.5V	1.2A
	300mΩ @ V _{GS} = 2.5V	1.04A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions

Features and Benefits

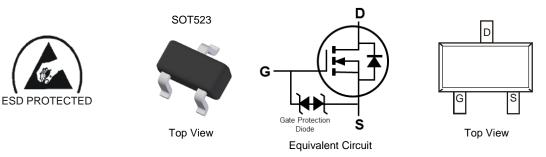
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

N-CHANNEL ENHANCEMENT MODE MOSFET

An Automotive-Compliant Part is Available Under Separate
Datasheet (DMN2310UTQ)

Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2310UT-7	SOT523	3000/Tape & Reel
DMN2310UT-13	SOT523	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

BE7	¥М				

BE7 = Product Type Marking Code

 \underline{YM} = Date Code Marking \overline{Y} = Year (ex: I = 2021)

M = Month (ex. 9 = September)

M = MOHH (ex. 9 = September)

Date Code Key												
Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	I	J	K	L	М	Ν	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

rs ent Functions



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	TA = +25°C T _A = +75°C	ID	1.2 1.0	A
Maximum Continuous Body Diode Forward Cur	rent (Note 6)	ls	0.6	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	= 1%)	Ідм	4.2	А	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	435	°C/W
Total Power Dissipation (Note 6)		PD	0.49	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	253	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

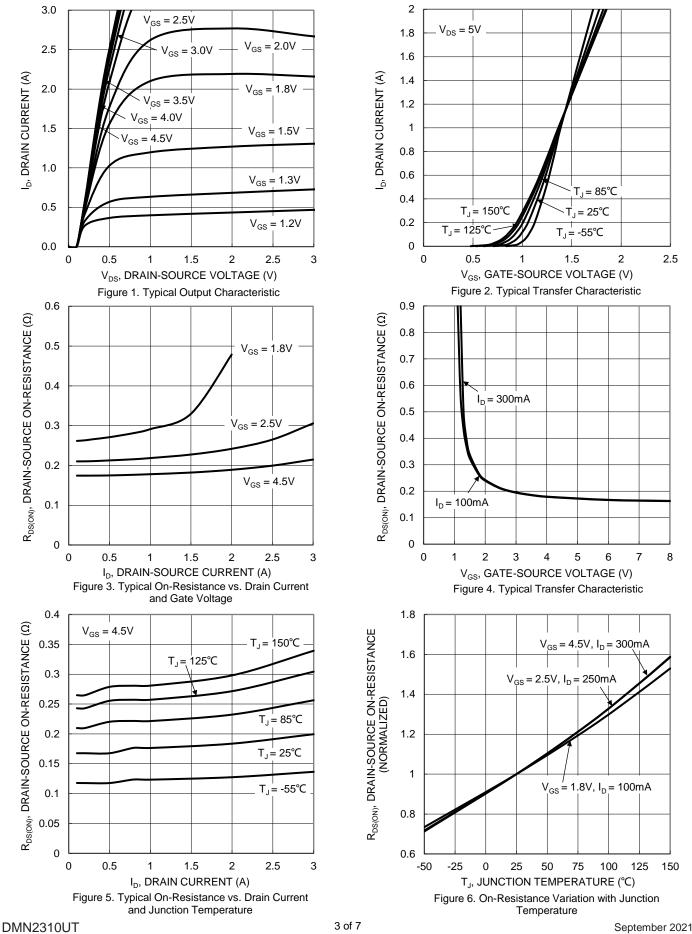
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	20		—	V	Vgs = 0V, Id = 250µA	
Zero Gate Voltage Drain Current	IDSS	_		1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_		10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			•	•			
Gate Threshold Voltage	Vgs(th)	0.45	_	0.95	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
		_	174	240		V _{GS} = 4.5V, I _D = 300mA	
Static Drain-Source On-Resistance	RDS(ON)	—	211	300	mΩ	$V_{GS} = 2.5V, I_D = 250mA$	
		_	263	400		$V_{GS} = 1.8V, I_D = 100mA$	
Diode Forward Voltage	Vsd	_	0.8	1.2	V	$V_{GS} = 0V$, $I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		38	—	pF		
Output Capacitance	Coss	_	10	—	pF	Vps = 10V, Vgs = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	6	—	pF		
Gate Resistance	Rg		1.42	_	kΩ	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg		0.7	—	nC		
Gate-Source Charge	Q _{gs}	—	0.1	—	nC	VGS = 4.5V, VDS = 10V, ID = 1A	
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC	D = TA	
Turn-On Delay Time	td(ON)	_	8	_	ns		
Turn-On Rise Time	t _R	_	138	—	ns	$V_{DD} = 10V, V_{GS} = 5V,$	
Turn-Off Delay Time	tD(OFF)	_	154	—	ns	$R_L = 1.7\Omega, R_G = 6\Omega$	
Turn-Off Fall Time	tF	_	180	_	ns	7	

Notes:

Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



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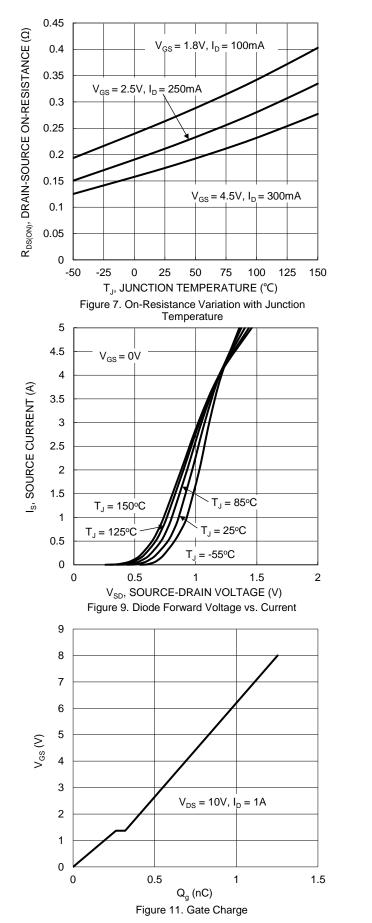


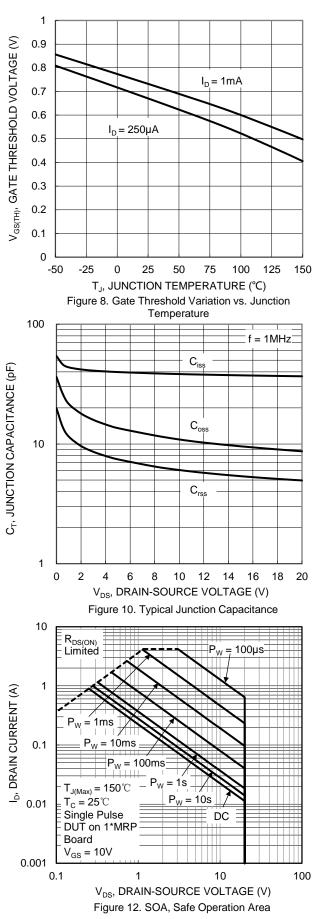
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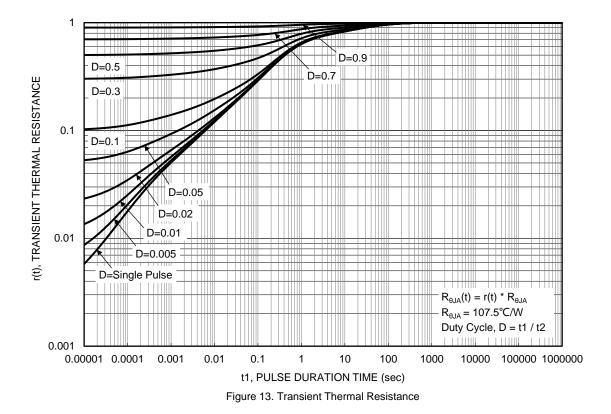






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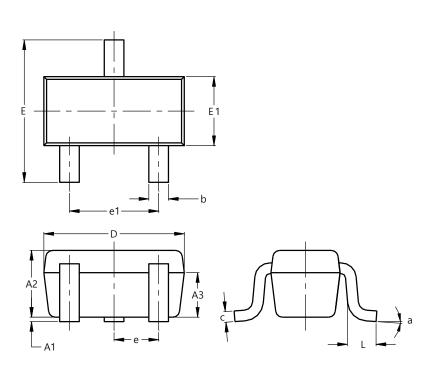






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

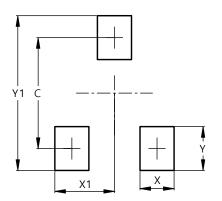


SOT523

SOT523							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.60	0.80	0.75				
A3	0.45	0.65	0.50				
b	0.15	0.30	0.22				
с	0.10	0.20	0.12				
D	1.50	1.70	1.60				
ш	1.45	1.75	1.60				
E1	0.75	0.85	0.80				
e		0.50 BS	С				
e1	0.90	1.10	1.00				
L	0.20	0.40	0.33				
а	0°		8°				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)					
С	1.29					
Х	0.40					
X1	0.70					
Y	0.51					
Y1	1.80					

SOT523



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